

3.3 V 256 K × 16 CMOS SRAM

Features

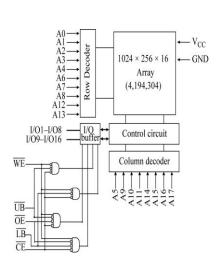
- Pin compatible with AS7C34098
- Industrial and commercial temperature
- Organization: 262,144 words × 16 bits
- Center power and ground pins
- High speed
 - 10/12/15/20 ns address access time
 - 4/5/6/7 ns output enable access time
- Low power consumption: ACTIVE
 - 650 mW/max @ 10 ns
- Low power consumption: STANDBY
 - 28.8 mW/max CMOS
- Individual byte read/write controls

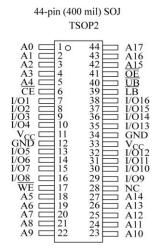
- Easy memory expansion with \overline{CE} , \overline{OE} inputs
- TTL- and CMOS-compatible, three-state I/O
- JEDEC standard packages
- 44-pin SOJ -400-mil
- 44-pin TSOP 2
- 48-pin Mini BGA
- ESD protection ≥ 2000 volts
- Latch-up current $\geq 200 \text{ mA}$

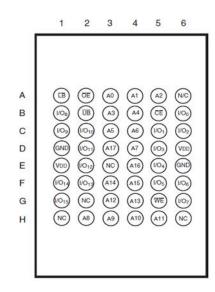
Logic block diagram

Pin arrangement for SOJ and TSOP 2

Bottom View 48BGA







Selection guide

		-10	-12	-15	-20	Unit			
Maximum address access time		10	12	15	20	ns			
Maximum output enable access time		4	5	6	7	ns			
Maximum operating current	Industrial	180	160	140	110	mA			
Waximum operating current	Commercial	170	150	130	100	mA			
Maximum CMOS standby current		8	8	8	8	mA			



Functional description

The AS7C34098A is a high-performance CMOS 4,194,304-bit Static Random Access Memory (SRAM) device organized as 262,144 words × 16 bits. It is designed for memory applications where fast data access, low power, and simple interfacing are desired.

Equal address access and cycle times (t_{AA}, t_{RC}, t_{WC}) of 10/12/15/20 ns with output enable access times (t_{OE}) of 4/5/6/7 ns are ideal for high-performance applications. The chip enable input \overline{CE} permits easy memory expansion with multiple-bank memory systems.

When \overline{CE} is high the device enters standby mode. The device is guaranteed not to exceed 28.8mW power consumption in CMOS standby mode. A write cycle is accomplished by asserting write enable (\overline{WE}) and chip enable (\overline{CE}). Data on the input pins I/O1–I/O16 is written on the rising edge of \overline{WE} (write cycle 1) or \overline{CE} (write cycle 2). To avoid bus contention, external devices should drive I/O pins only after outputs have been disabled with output enable (\overline{OE}) or write enable (\overline{WE}).

A read cycle is accomplished by asserting output enable (\overline{OE}) and chip enable (\overline{CE}) , with write enable (\overline{WE}) high. The chip drives I/O pins with the data word referenced by the input address. When either chip enable or output enable is inactive, or write enable is active, output drivers stay in high-impedance mode.

The device provides multiple center power and ground pins, and separate byte enable controls, allowing individual bytes to be written and read. \overline{LB} controls the lower bits, I/O1–I/O8, and \overline{UB} controls the higher bits, I/O9–I/O16.

All chip inputs and outputs are TTL- and CMOS-compatible, and operation is for 3.3V (AS7C34098A) supply. The device is available in the JEDEC standard 400-mil, 44-pin SOJ, TSOP 2.

Absolute maximum ratings

Parameter	Symbol	Min	Max	Unit
Voltage on V _{CC} relative to GND	V_{t1}	-0.50	+5.0	V
Voltage on any pin relative to GND	V_{t2}	-0.50	V _{CC} +0.50	V
Power dissipation	P_{D}	_	1.5	W
Storage temperature (plastic)	T _{stg}	-65	+150	°C
Ambient temperature with V _{CC} applied	T _{bias}	-55	+125	°C
DC current into outputs (low)	I _{OUT}	_	±20	mA

Note: Stresses greater than those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions outside those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Truth table

CE	WE	OE	LB	UB	I/O1–I/O8	I/O9–I/O16	Mode
Н	X	X	X	X	High Z	High Z	Standby (I _{SB} , I _{SB1})
L	Н	Н	X	X	III1. 7	III. I. Z	Outmut disable (I)
L	X	X	Н	Н	High Z	High Z	Output disable (I _{CC})
			L	Н	D_{OUT}	High Z	
L	Н	L	Н	L	High Z	D _{OUT}	Read (I _{CC})
			L	L	D _{OUT}	D _{OUT}	
			L	Н	D _{IN}	High Z	
L	L	X	Н	L	High Z	D_{IN}	
			L	L	D_{IN}	D_{IN}	Write (I _{CC})

Key: X = Don't care, L = Low, H = High.



Recommended operating conditions

Parameter		Symbol	Min	Typical	Max	Unit
Supply voltage		V _{CC} (10/12/15/20)	3.0	3.3	3.6	V
Input voltage	V _{IH} **	2.0	_	$V_{CC} + 0.5$	V	
input voltage		V _{IL} *	-0.5	_	0.8	V
Ambient operating temperature	commercial	T_{A}	0	_	70	°C
7 moterit operating temperature	industrial	T_{A}	-40	_	85	°C

DC operating characteristics (over the operating range) I

			-10		-10 -12		12	-	15	-20		
Parameter	Symbol	Test conditions		Min	Max	Min	Max	Min	Max	Min	Max	Unit
Input leakage current	$ I_{LI} $	$V_{CC} = Max$ $V_{IN} = GND \text{ to } V_{CC}$			1	_	1	_	1	_	1	μΑ
Output leakage current	I _{LO}	$\frac{V_{CC} = Max}{CE = V_{\underline{IH}} \text{ or } \overline{OE} = }$ or $\overline{WE} = V_{IL}$ $V_{\underline{I/O}} = GND \text{ to } V_{\underline{O}}$	_	1	_	1	_	1	_	1	μА	
Operating	$V_{CC} = Max$		Industrial	-	180	_	160	_	140	_	110	mA
power supply current	I_{CC}	$\overline{\text{CE}} \le \text{V}_{\text{IL}}, \text{ f} = \text{f}_{\text{max}} \text{I}_{\text{OUT}} = 0 \text{mA}$	Commercial	-	170	-	150	-	130	-	100	mA
C4 and Illian in a second	I_{SB}	$\frac{V_{CC} = Max}{CE \ge V_{IH}, f = Ma}$	ıx	_	60	_	60	_	60	_	60	mA
Standby power supply current	I_{SB1}	$V_{CC} = Max$ $\overline{CE} \ge V_{CC} - 0.2V, V_{IN} \ge V_{CC}$ $V_{IN} \le 0.2V, f = 0$		_	8	_	8	_	8	_	8	mA
Output voltage	Output voltage V_{OL} $I_{OL} = 8 \text{ mA}, V_{CC} = \text{Min}$		Min	_	0.4	_	0.4	-	0.4	_	0.4	V
Output voltage	V _{OH}	$I_{OH} = -4 \text{ mA}, V_{CC} =$	Min	2.4	_	2.4	_	2.4	_	2.4	_	V

Capacitance (f = 1MHz, $T_a = 25^{\circ}$ C, $V_{CC} = NOMINAL$)²

Parameter	Symbol	Signals	Test conditions	Max	Unit
Input capacitance	C _{IN}	A, CE, WE, OE, UB, LB	$V_{IN} = 0V$	6	pF
I/O capacitance	C _{I/O}	I/O	$V_{IN} = V_{OUT} = 0V$	8	pF

 $^{^*}$ V_{IL} min = -1.0V for pulse width less than 5ns. V_{IH} max = $V_{CC}\,$ + 2.0V for pulse width less than 5ns.



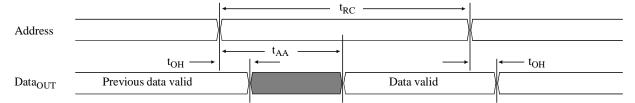
Read cycle (over the operating range)^{3,9}

		-1	10	-1	12	-1	15	-2	20		
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Unit	Notes
Read cycle time	t _{RC}	10	-	12	_	15	1	20	1	ns	
Address access time	t_{AA}	_	10	_	12	_	15	_	20	ns	
Chip enable (\overline{CE}) access time	t _{ACE}	_	10	_	12	_	15	_	20	ns	
Output enable (OE) access time	t _{OE}	_	4	_	5	_	6	_	7	ns	
Output hold from address change	t _{OH}	3	_	3	_	3	_	3	_	ns	5
CE Low to output in low Z	t _{CLZ}	3	_	3	_	3	_	3	_	ns	4, 5
CE High to output in high Z	t _{CHZ}	_	5	_	6	_	7	_	9	ns	4, 5
OE Low to output in low Z	t _{OLZ}	0	_	0	_	0	_	0	_	ns	4, 5
OE High to output in high Z	t _{OHZ}	_	5	_	6	_	7	_	9	ns	4, 5
LB, UB access time	t _{BA}	_	5	_	6	_	7	_	8	ns	
LB, UB Low to output in low Z	t _{BLZ}	0	_	0	_	0	_	0	_	ns	
LB, UB High to output in high Z	t _{BHZ}	_	5	_	6	_	7	_	9	ns	
Power up time	t_{PU}	0	_	0	_	0	_	0	_	ns	5
Power down time	t _{PD}	_	10	_	12	_	15	_	20	ns	5

Key to switching waveforms

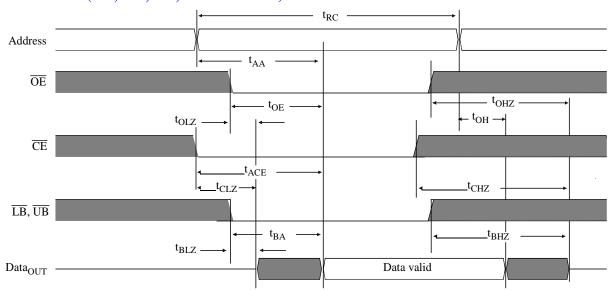
Rising input Falling input Undefined/don't care

Read waveform 1 (address controlled)^{6,7,9}





Read waveform 2 (\overline{CE} , \overline{OE} , \overline{UB} , \overline{LB} controlled)^{6,8,9}

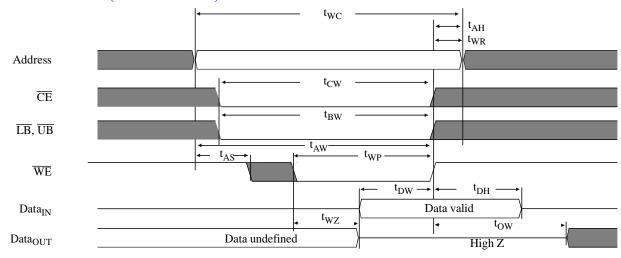


Write cycle (over the operating range)¹⁰

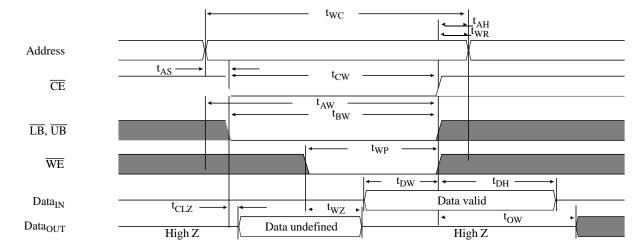
		_	10	-	12	_	15	-	20		
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Unit	Note
Write cycle time	t _{WC}	10	_	12	_	15	_	20	_	ns	
Chip enable (CE) to write end	t _{CW}	7	_	8	_	10	_	12	_	ns	
Address setup to write end	t _{AW}	7	_	8	_	10	_	12	_	ns	
Address setup time	t _{AS}	0	_	0	_	0	_	0	_	ns	
Write pulse width ($\overline{OE} = High$)	t _{WP1}	7	_	8	_	10	_	12	_	ns	
Write pulse width $(\overline{OE} = Low)$	t _{WP2}	10	_	12	_	15	_	20	_	ns	
Write recovery time	t _{WR}	0	_	0	_	0	_	0	_	ns	
Address hold from end of write	t _{AH}	0	_	0	_	0	_	0	_	ns	
Data valid to write end	t _{DW}	5	_	6		7	_	9	_	ns	
Data hold time	t _{DH}	0	_	0	_	0	_	0	_	ns	4, 5
Write enable to output in High-Z	t _{WZ}	0	5	0	6	0	7	0	9	ns	4, 5
Output active from write end	t _{OW}	3	_	3	_	3	_	3	_	ns	4, 5
Byte enable Low to write end	t _{BW}	7	_	8	1	10	_	12	_	ns	4, 5



Write waveform $1(\overline{WE} \text{ controlled})^{10}$

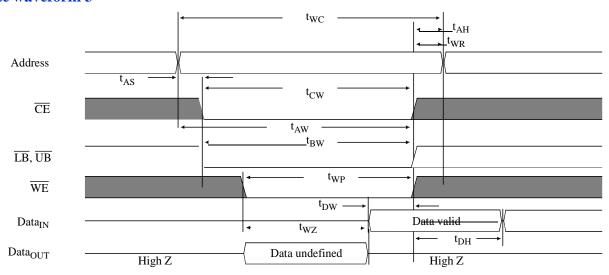


Write waveform 2 (CE controlled)10





Write waveform 3 10



AC test conditions

- Output load: see Figure B.
- Input pulse level: GND to 3.0V. See Figure A.
- Input rise and fall times: 2 ns. See Figure A.
- Input and output timing reference levels: 1.5V.

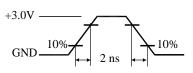
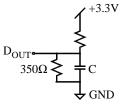
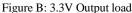


Figure A: Input pulse





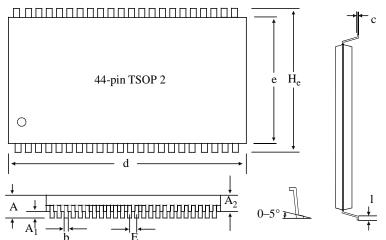
D_{OU} \longrightarrow O_{OU}

Notes

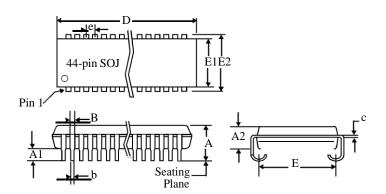
- 1 During V_{CC} power-up, a pull-up resistor to V_{CC} on \overline{CE} is required to meet I_{SB} specification.
- 2 This parameter is sampled, but not 100% tested.
- 3 For test conditions, see AC Test Conditions, Figures A and B.
- t_{CLZ} and t_{CHZ} are specified with $t_{CL} = 5$ pF as in Figure B. Transition is measured ± 500 mV from steady-state voltage.
- $5\qquad \hbox{This parameter is guaranteed, but not tested.}$
- 6 WE is High for read cycle.
- 7 $\overline{\text{CE}}$ and $\overline{\text{OE}}$ are Low for read cycle.
- 8 Address valid prior to or coincident with $\overline{\text{CE}}$ transition Low.
- 9 All read cycle timings are referenced from the last valid address to the first transitioning address.
- 10 All write cycle timings are referenced from the last valid address to the first transitioning address.
- 11 C=30pF, except on High Z and Low Z parameters, where C=5pF.



Package dimensions



	44-pin '	TSOP 2				
	Min (mm)	Max (mm)				
A		1.2				
$\mathbf{A_1}$	0.05	0.15				
A ₂	0.95	1.05				
b	0.3	0.45				
c	0.12	0.21				
d	18.31	18.52				
e	10.06	10.26				
H _e	11.68	11.94				
E	0.80 (typical)					
l	0.40	0.60				



	44-pin SO	J 400 mils
	Min(mils)	Max(mils)
A	0.128	0.148
A1	0.025	-
A2	0.105	0.115
В	0.026	0.032
b	0.015	0.020
c	0.007	0.013
D	1.120	1.130
E	0.370	NOM
E 1	0.395	0.405
E2	0.435	0.445
e	0.050	NOM



Outline of 48BGA

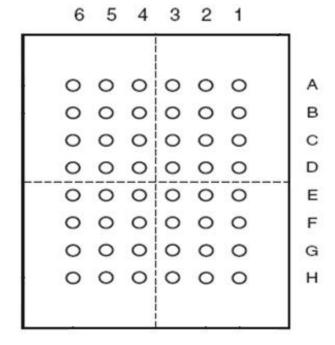
1 2 3 4 5 6

A
B
C
D
E
F
G
H

Top View



Bottom View



Notes:

1. Controlling dimensions are in millimeters.

BGA 8mm x 10mm
MILLIMETERS

Sym.	Min.	Тур.	Max.			
Α	35/63	<u>=</u> =31	1.20			
A1	0.24	2_2	0.30			
A2	0.60	_	_			
D	9.90	10.00	10.10			
D1	5	.25 BS	С			
E	7.90	8.00	8.10			
E1	3	.75 BS	С			
е	0.75 BSC					
b	0.30	0.35	0.40			



Ordering Codes

Package	Temperature	10 ns	12	15 ns	20 ns
SOJ	Commercial	AS7C34098A-10JC	AS7C34098A-12JC	AS7C34098A-15JC	AS7C34098A-20JC
	Industrial	AS7C34098A-10JI	AS7C34098A-12JI	AS7C34098A-15JI	AS7C34098A-20JI
BGA	Industrial	AS7C34098A-10BIN			
TSOP 2	Commercial	AS7C34098A-10TC	AS7C34098A-12TC	AS7C34098A-15TC	AS7C34098A-20TC
1501 2	Industrial	AS7C34098A-10TI	AS7C34098A-12TI	AS7C34098A-15TI	AS7C34098A-20TI

Note: Add suffix 'N' to the above part numbers for Lead Free Parts. (Ex: AS7C34098A - 10TCN)

Part numbering system

AS7C	X	4098A	-XX	J/T or B	X	X
SRAM prefix	Voltage: 3 - 3.3V CMOS	Device number	Access time	Packages: J: SOJ 400 mil T: TSOP 2 B: BGA	Temperature ranges: C: Commercial, 0°C to 70°C I: Industrial, –40°C to 85°C	





Alliance Memory, Inc. 511 Taylor Way, San Carlos, CA 94070 Tel: 650-610-6800 Fax: 650-620-9211

www.alliancememory.com

Copyright © Alliance Memory

All Rights Reserved

Part Number: AS7C34098A Document Version: v. 2.2

© Copyright 2003 Alliance Memory, Inc. All rights reserved. Our three-point logo, our name and Intelliwatt are trademarks or registered trademarks of Alliance. All other brand and product names may be the trademarks of their respective companies. Alliance reserves the right to make changes to this document and its products at any time without notice. Alliance assumes no responsibility for any errors that may appear in this document. The data contained herein represents Alliance's best data and/or estimates at the time of issuance. Alliance reserves the right to change or correct this data at any time, without notice. If the product described herein is under development, significant changes to these specifications are possible. The information in this product data sheet is intended to be general descriptive information for potential customers and users, and is not intended to operate as, or provide, any guarantee or warrantee to any user or customer. Alliance does not assume any responsibility arising out of the application or use of any product described herein, and disclaims any express or implied warranties related to the sale and/or use of Alliance products including liability or warranties related to fitness for a particular purpose, merchantability, or infringement of any intellectual property rights, except as express agreed to in Alliance's Terms and Conditions of Sale (which are available from Alliance). All sales of Alliance products are made exclusively according to Alliance's Terms and Conditions of Sale. The purchase of products from Alliance does not convey a license under any patent rights, copyrights; mask works rights, trademarks, or any other intellectual property rights of Alliance or third parties. Alliance does not authorize its products for use as critical components in life-supporting systems where a malfunction or failure may reasonably be expected to result in significant injury to the user, and the inclusion of Alliance products in such life-supporting systems implies that the manufactu

AMEYA360 Components Supply Platform

Authorized Distribution Brand:

























Website:

Welcome to visit www.ameya360.com

Contact Us:

> Address:

401 Building No.5, JiuGe Business Center, Lane 2301, Yishan Rd Minhang District, Shanghai , China

> Sales:

Direct +86 (21) 6401-6692

Email amall@ameya360.com

QQ 800077892

Skype ameyasales1 ameyasales2

Customer Service :

Email service@ameya360.com

Partnership :

Tel +86 (21) 64016692-8333

Email mkt@ameya360.com